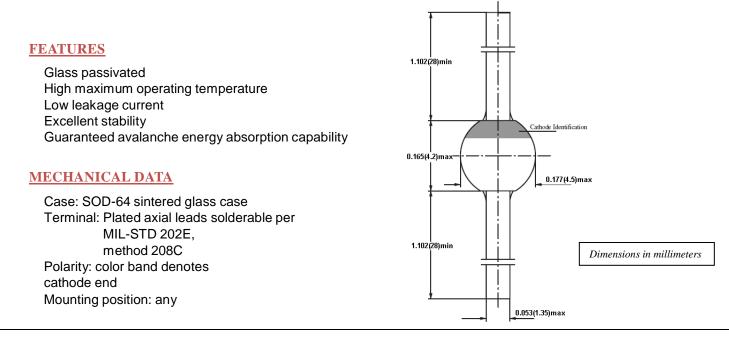


AMS-G2M

Technical Specifications



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half-wave, 60HZ, resistive or inductive load rating at 25 C, unless otherwise stated)

	SYMBOL	BYM26E	units
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	1000	V
Maximum RMS Voltage	V _{RMS}	700	V
Maximum DC blocking Voltage	V _{DC}	1000	V
Reverse Breakdown Voltage at $I_R = 0.1 \text{mA}$	V _{(BR)R}	1100min	V
Maximum Average Forward Rectified Current and Ttp=55 C; lead length=10mm	I _{FAV}	2.3	А
Peak Forward Surge Current at t=10ms half sine wave	I _{FSM}	45	А
$\begin{array}{llllllllllllllllllllllllllllllllllll$	V _F	2.65	V
Maximum DC Reverse CurrentTa = 25 Cat rated DC blocking voltageTa = 150 C	I _R	10 150	A A
Maximum Reverse Recovery Time (Note 1)	Trr	75	nS
Non Repetitive Reverse Avalanche Energy	E _R	10	mJ
Diode Capacitance at f=1MHz,V _R =0V	C _d	75	pF
Typical Thermal Resistance (Note 2)	R _{th(ja)}	75	K/W
Storage and Operating Junction Temperature	Tstg, Tj	-65 to +175	°C

Note:

1. Reverse Recovery Condition $I_F = 0.5A$, $I_R = 1.0A$, $I_{RR} = 0.25A$

2. Device mounted on an epoxy-glass printed-circuit board, 1.5mm thick; thickness of Cu-layer \geq 40 μ m

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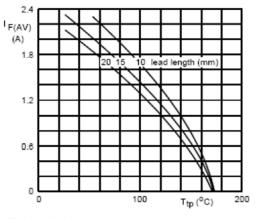


Fig.1 Maximum average forward current as a function of tie-point temperature (including losses due to reverse leakage).

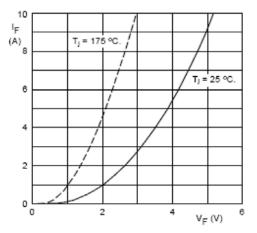


Fig. 3 Forward current as a function of forward voltage; maximum values.

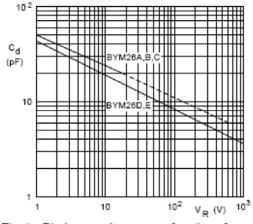


Fig. 5 Diode capacitance as a function of reverse voltage; typical values.

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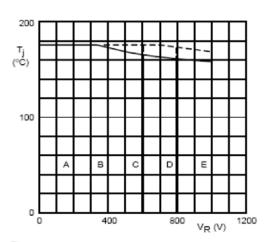


Fig. 2 Maximum permissible junction temperature as a function of reverse voltage.

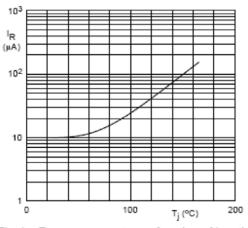


Fig.4 Reverse current as a function of junction temperature; maximum values.

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